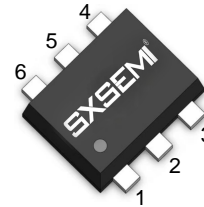
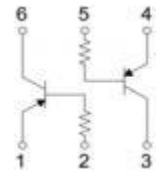


**FEATURES**

- I Two DTA114T chips in a package

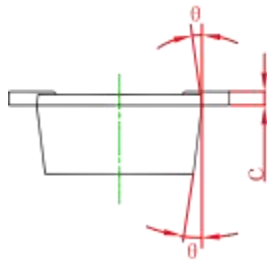
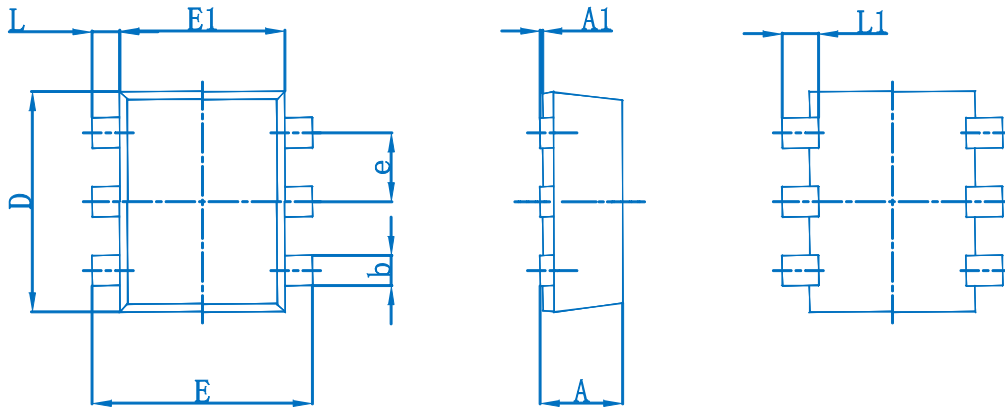
**SOT-563**

**Marking: B4**

**Absolute maximum ratings ( $T_a=25^\circ\text{C}$ )**

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-100	mA
$P_C$	Collector Power Dissipation	150	mW
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55-+150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$  unless otherwise specified)**

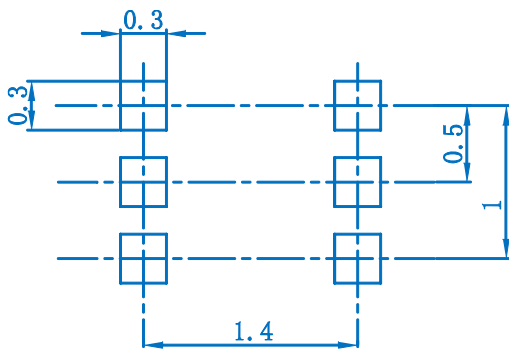
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-50\text{V}, I_E=0$			-0.5	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4\text{V}, I_C=0$			-0.5	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	100		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.3	V
Transition frequency	$f_T$	$V_{CE}=-10\text{V}, I_C=-5\text{mA}, f=100\text{MHz}$		250		MHz
Input resistance	$R_1$	-	7		13	$\Omega$

**SOT-563 Package Outline Dimensions**



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	10°REF.		10°REF.	

**SOT-563 Suggested Pad Layout**



- Note:**
1. Controlling dimension: in millimeters.
  2. General tolerance: ±0.05mm.
  3. The pad layout is for reference purposes only.